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(54) Title: APPLICATIONS OF SEMICONDUCTOR NANO-SIZED PARTICLES FOR PHOTOLITHOGRAPHY

(57) Abstract: Semiconductor nano-sized particles possess unique optical properties, which make them ideal candidates for various applications in the UV photolithography. In this patent several such applications, including using semiconductor nano-sized particles or semiconductor nano-sized particle containing materials as highly refractive medium in immersion lithography, as anti-reflection coating in optics, as pellicle in lithography and as sensitizer in UV photoresists are described.

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## APPLICATIONS OF SEMICONDUCTOR NANO-SIZED PARTICLES FOR PHOTOLITHOGRAPHY

### CROSS-REFERENCES TO RELATED APPLICATIONS

[0001] This application claims the benefit of priority from provisional application no. 60/451,240 filed 3/04/03, incorporated herein by reference.

[0002] This application is related to US patent No. US 6,291,110 B1, Cooper *et al.* entitled "Photolithographic System For Exposing A Wafer Using A Programmable Mask"; and commonly-assigned provisional application No. \_\_\_\_\_, filed \_\_\_\_\_ entitled "Programmable photolithographic mask and reversible photo-bleachable materials based on nano-sized semiconductor particles and their applications" to Z. Chen *et al.*

### FIELD

[0003] This technology herein relates to photolithography, and more particularly to applications of semiconductor nano-sized particles in photolithography, and even more particularly to applications of semiconductor nano-sized particles as highly refractive media in immersion lithography, as anti-reflection coating, as pellicle, and as sensitizer in UV photoresists.

### STATEMENT REGARDING FEDERALLY SPONSORED RESEARCH OR DEVELOPMENT

[0004] Not applicable.

## BACKGROUND AND SUMMARY

### Lithography

[0005] Generally, lithography is used to transfer a specific pattern onto a surface. Lithography can be applied to transfer a variety of patterns including, for example, painting, printing, and the like. More recently, lithographic techniques have become widespread for use in "microfabrication" -- a major (but non-limiting) example of which is the manufacture of integrated circuits such as computer chips.

[0006] In a typical microfabrication operation, lithography is used to define patterns for miniature electrical circuits. Lithography defines a pattern specifying the location of metal, insulators, doped regions, and other features of a circuit printed on a silicon wafer or other substrate. The resulting circuit can perform any of a number of different functions. For example, an entire computer can be placed on a chip.

[0007] A primary lithography system includes a wafer stepper, a photomask and photoresist. A wafer stepper generally consists of a ultraviolet (UV) light source, a photomask holder, an optical system for projecting and demagnifying the image of the mask onto a photoresist-coated wafer, and a stage to move the wafer. Conventional lithography also generally requires a photomask -- a quartz substrate with chrome patterns on one surface. The chrome patterns form a perfect master of the pattern to be inscribed on one layer of a chip. Also it requires photoresist to receive the light pattern generated by the mask.

[0008] Improvements in lithography have been mainly responsible for the explosive growth of computers in particular and the semiconductor industry in general. The major improvements in lithography are mainly a

result of a decrease in the minimum feature size (improvement in resolution). This improvement allows for an increase in the number of transistors on a single chip (and in the speed at which these transistors can operate). For example, the computer circuitry that would have filled an entire room in 1960's technology can now be placed on a silicon "die" the size of a thumbnail. A device the size of a wristwatch can contain more computing power than the largest computers of several decades ago.

**[0009]** The resolution of a photolithography system is described by the Rayleigh equation:

$$d = k_1 \lambda / NA$$

where  $d$  is the minimum feature size,  $\lambda$  is the wavelength,  $NA$  is the numerical aperture of the optical system and  $k_1$  is a constant determined by a specific system. For a certain wavelength and a certain optical design, the only way to improve the resolution is to increase the numerical aperture. The numerical aperture is defined as:

$$NA = n \sin \theta$$

where  $n$  is the refraction index of the relative medium and  $\theta$  is the half angle of the cone of rays received by the entrance pupil. High  $NA$  indicates high light collecting or light focusing power. It is rather straightforward to see that the resolution is proportional the refractive index of the medium.

#### Semiconductor Nano-sized particles

**[0010]** Nano-sized particles are loosely defined as powders with small diameters for example ranging from a few hundred nanometers or less down to a few angstroms. Since they have generally only been the focus of research in the last two decades, there is little standardization, and they take many different names including quantum dot, quantum sphere, quantum crystallite, nano-crystal, micro-crystal, colloidal particle, nano-cluster, Q-

particle or artificial atom. Due to their small size, they often possess dramatically different physical properties compared to their bulk counterparts. Nano-sized particles have a wide range of applications including metallurgy, chemical sensors, pharmaceuticals, painting, and cosmetics. As a result of the rapid development in synthesis methods in the last two decades, they have now entered into microelectronic and optical applications. Nano-sized particles with sizes less than 5 nm have been synthesized from a variety of semiconductors, examples include C, Si, Ge, CuCl, CuBr, CuI, AgCl, AgBr, AgI, Ag<sub>2</sub>S, CaO, MgO, ZnO, ZnS, HgS, ZnSe, CdS, CdSe, CdTe, HgTe, PbS, BN, AlN, GaN, GaP, GaAs, GaSb, InP, InAs, In<sub>x</sub>Ga<sub>1-x</sub>As, SiC, Si<sub>1-x</sub>Ge<sub>x</sub>, Si<sub>3</sub>N<sub>4</sub>, ZrN, CaF<sub>2</sub>, YF<sub>3</sub>, Al<sub>2</sub>O<sub>3</sub>, SiO<sub>2</sub>, TiO<sub>2</sub>, Cu<sub>2</sub>O, Zr<sub>2</sub>O<sub>3</sub>, SnO<sub>2</sub>, YSi<sub>2</sub>, GaInP<sub>2</sub>, Cd<sub>3</sub>P<sub>2</sub>, Fe<sub>2</sub>S, Cu<sub>2</sub>S, CuIn<sub>2</sub>S<sub>2</sub>, MoS<sub>2</sub>, In<sub>2</sub>S<sub>3</sub>, Bi<sub>2</sub>S<sub>3</sub>, CuIn<sub>2</sub>Se<sub>2</sub>, In<sub>2</sub>Se<sub>3</sub>, HgI<sub>2</sub>, PbI<sub>2</sub>, Lanthanoids oxides, etc. They have revealed very interesting optical properties.

**[0011]** Semiconductor materials have the so called bandgaps. The electron band below the bandgap is called valence band (VB) and the electron band above the bandgap is called conduction band (CB). The manifestation of a bandgap in optical absorption is that only photons with energy larger than the bandgap are absorbed. A photon with sufficient energy excites an electron from the top of valence band to the bottom of conduction band, leaving an empty state, a hole, at the top of the valence band.

**[0012]** There are several major advantages of using semiconductor nano-sized particles in photolithography. First, the bandgap of semiconductor nano-sized particles can be tailored by their size. In a certain range the smaller the size, the larger the bandgap. The bandgap determines the working wavelength.

[0013] Second, the refractive index can be very high near the bandgap. Actually some semiconductors have the highest refractive indices. For example wurzite  $\text{TiO}_2$  has a refractive index of 2.4, and wurzite GaN has a refractive index about 2.6 near the bandgap. The refractive indices of common optical materials such as fused silica and quartz used in the UV lithography are around 1.5. This high refractive index is desirable for highly refractive medium immersion lithography and optical coating.

[0014] Third, nano-sized particles can be easily coated onto optics or wafers in the form of a thin film. They are, therefore, very simple to handle and produce much less contamination. Because of the polycrystalline nature of nano-sized particle films, there is less concern about matching the thermal expansion coefficients between the coating and the optics. Applying nano-sized particles by coating provides least disturbance to the existing lithography system.

[0015] Fourth, semiconductors nano-sized particles can reach sizes much smaller than the working wavelength. Currently, a large number of semiconductors can be fabricated into nano-sized particles smaller than 5nm in diameter. Hence the scattering from the nanoparticles is negligible and size fluctuation of nano-sized particles does not affect the final scattered and transmitted light.

[0016] Fifth, in a broad sense semiconductors can possess bandgaps as high as 12eV, corresponding to a wavelength of 100nm. For 157nm lithography and beyond, few materials can withstand the radiation except certain semiconductors. Nano-sized particles offer a solution for the optics in these wavelengths.

[0017] Lastly, many semiconductor nano-sized particles can be produced rather inexpensively. Therefore, the overall cost will likely be lower than conventional methods.

[0018] We propose several applications of semiconductor nano-sized particles in lithography. Such as highly refractive medium in immersion lithography, optical coating, pellicle material, and sensitizer in photoresists.

#### BRIEF DESCRIPTION OF THE DRAWINGS

[0019] These and other features and advantages will be better and more completely understood by referring to the following detailed description of presently preferred illustrative embodiments in conjunction with the drawings, of which:

[0020] Figure 1 shows an exemplary illustrative non-limiting optical structure to achieve high resolution by inserting a layer of high refractive index semiconductor nano-sized particle layer between the photomask and the next optics in a projection photolithography system;

[0021] Figure 2 shows an exemplary illustrative non-limiting optical structure to achieve high resolution by inserting a thin layer of high refractive index containing semiconductor nano-sized particle between the final optics and the photoresist in a projection photolithography system;

[0022] Figure 3 shows an exemplary illustrative non-limiting antireflection coating for optical lens with a thickness of the coating of  $\lambda/4n$  for maximum transmission;

[0023] Figure 4a is an exemplary illustrative non-limiting photoresist with semiconductor nano-sized particles as sensitizer;

[0024] Figure 4b shows the exemplary physical process in which photo-generated electron or hole are transferred out of the particle via surface bonded acceptor or donor; and

[0025] Figure 4c demonstrates the exemplary illustrative physical process, i.e. Auger photo-ionization, in which electrons or holes are ejected out the particle as a result of the incoming photon.

#### DETAILED DESCRIPTION OF PRESENTLY PREFERRED EXAMPLE ILLUSTRATIVE NON-LIMITING IMPLEMENTATIONS

[0026] It is shown in the Rayleigh equation that the resolution of a lithography system is proportionally dependant on the refractive index of the relevant medium. There are several examples of achieving high resolution by immersion in high refractive index liquid materials. However, the fact that all liquids used in the liquid immersion lithography have refractive index smaller than 1.5 limits the final achievable resolution. Solid immersion lithography has been proposed to achieve higher refractive index.

[0027] Nano-sized particles, as mentioned before, could offer much higher refractive indices. Therefore, nano-sized particles, or mixtures of nano-sized particles with certain liquid, polymer, gel or solid material can improve the resolution in both liquid and solid immersion lithography.

[0028] A first exemplary illustrative non-limiting application of nano-sized particle as highly refractive medium in lithography is demonstrated in Fig. 1. In projection lithography, a layer containing nano-sized particles is inserted between the photomask and the immediate next lens. This layer can be coated onto either the photomask or the lens itself.



For 365nm lithography, this layer may comprise ZnO or GaN nano-sized particles. For 193nm lithography, it may comprise  $Mg_xZn_{1-x}O$  or AlN or BN nano-sized particles. The highly refractive layer has more efficiency in collecting the light transmitted through the photomask. Numerical aperture, as defined by  $NA = n \sin \theta$ , describes the light-gathering power of a lens. In Fig.1, by inserting a high refractive layer between the mask and the first lens, the numerical aperture is increased by a factor of  $n$ , comparing to air. In air, NA cannot be larger than 1, while with this coating NA can easily exceed 1. For example if  $TiO_2$  nano-sized particles are used, even with a  $NA=0.5$  in air, the final NA is 1.3.

**[0029]** This high light collecting efficiency offers great advantages to the lithography system. First, if the geometry of the entire optical system is kept the same, this added layer will increase the final resolution by a factor of  $n$ . If the numerical aperture, i.e. the resolution, is kept the same, then the diameter of the optical system can be reduced by a factor of  $n$  and therefore the overall cost of the system can be reduced. In particularly, in programmable lithography, reduced size of optics means increase in the throughput by roughly  $n^2$  (see "Photolithographic System For Exposing A Wafer Using A Programmable Mask" by G. Cooper et. al., US patent number US 6,291,110 B1).

**[0030]** Another exemplary illustrative implementation is shown in Fig. 2. In this non-limiting example the high refractive index nano-sized particle containing layer is applied at the wafer end of the lithography system. A layer containing nano-sized particle is inserted between the photoresist and the exit of the projection optical system. This layer may be simply deposited or spun on top of the photoresist. This layer may also be formed by immersing the space between the final optics and photoresist

with nano-sized particle containing highly refractive liquid, polymer or gel. This layer may also be formed by continuously flowing highly refractive liquid or gel through the space between the final optics and the photoresist. The highly refractive liquid may contain nano-sized particles and water. Again, as indicated by the Rayleigh equation, the resolution of the system is increased by a factor of  $n$ . For semiconductor nano-sized particles with refractive index bigger than 2.5, this can be a significant improvement.

[0031] Another exemplary illustrative non-limiting arrangement is to coat the numerical aperture limiting optics. In an imaging system the numerical aperture is usually limited by the entrance optics. In some systems, the numerical aperture may be limited by some intermediated optics. To improve the overall NA, the specific optics may be coated with highly refractive semiconductor nano-sized particles containing material.

[0032] Another exemplary illustration is to fill the entire optical system with semiconductor nano-sized particles or mixture of nano-sized particle with liquid, polymer, gel or solid. Light spreads more in the low refractive index material than in the high refractive index material, filling up the entire space with high refractive index material confines the light path to a tighter distribution. Therefore, it can reduce the diameter of the optical design further. This is particularly important to the programmable lithography because smaller optics increase the throughput, see "Photolithographic System For Exposing A Wafer Using A Programmable Mask" by G. Cooper et. al., US patent number US 6,291,110 B1.

[0033] For certain wavelengths in lithography such as 193nm and 157nm, few materials can withstand the highly energetic radiation except some wide bandgap semiconductors such as MgO and AlN. The high refractive index in these semiconductors also offers certain advantages. For

example, it will require less thickness to achieve certain optical path, which is defined as refractive index times the thickness. Smaller thickness in turn results in less absorption.

[0034] An exemplary illustration of applying semiconductor nano-sized particles for optical coating is the anti-reflection coating of optical lenses, as demonstrated in Fig. 3. Anti-reflection coating has an optical path of a quarter of the wavelength, so the reflection is minimized. Of course, the coating material itself has to cause little or no absorption at the working wavelength. For optics working at 193nm, Nano-sized particles such as  $Mg_xZn_{1-x}O$ , BN, AlN,  $CaF_2$ ,  $MgF_2$ , and  $SiO_2$  may be used as the coating material because they all have bandgap larger than the photon energy. For 157nm lithography, AlN,  $SiO_2$  nano-sized particles may be used. Nano-sized particles can be mixed with certain decomposable polymer matrix, spun on to the optics and then the matrix can be removed through chemical processes. Nano-sized particles may also be grown directly on the optics by various known growth methods.

[0035] Another exemplary illustration is to use the semiconductor nano-sized particles as pellicle materials. A pellicle provides protection for a photomask against dust particles. The pellicle itself may be transparent to the light and have certain mechanical strength. For 193nm pellicle, nano-sized particles such as  $Mg_xZn_{1-x}O$ , BN, AlN,  $CaF_2$ ,  $MgF_2$ ,  $SiO_2$ , may be used as candidate materials. For 157nm lithography, AlN,  $SiO_2$  nano-sized particles may be used as candidate materials. Few hundred micrometers of close-packed nano-sized particles may be grown on a substrate, such as thin glass plate using suitable methods. High pressure may be applied after the deposition to assure mechanical strength. Then the substrate can be etched

away by selective etching, such as HF acid etching, leaving the free standing film as the pellicle.

**[0036]** An exemplary illustration of applying semiconductor nano-sized particles as a sensitizer in photoresist is shown in Fig. 4. Nano-sized particles with certain bandgap(s) are mixed with certain polymers as seen in the Fig. 4a. Upon absorption of a photon, the resulted electron or hole may be transferred out of the nano-sized particle into surrounding polymers via surface states or surface bonded acceptor or donor. The transferred electrons or holes can then break or form bonds in the polymer and alter its solubility of the polymer to developers. This type of photoresist can be used at wavelength shorter than 193nm where it is difficult to find conventional photoresists.

**[0037]** If nano-sized particles are small enough, multi-body interactions such as Auger photo-ionization can be significant. As depicted in Fig. 4b, in an Auger process, a photon generates a pair of electron and hole, when the pair recombines, it transfer its energy and momentum to another electron or hole. When multiple Auger effects occur simultaneously, some of electrons or holes can gain enough energy to be ejected out of the particle into the surrounding environment. This process is described in the publication entitled "Fluorescence Intermittency In Single Cadmium Selenide Nanocrystals" to M. Nirmal *et. al.*, Nature, 1996, 383, pp.802-804. The ejected energetic electrons lose their energy by breaking chemical bonds of the polymers. The broken bonds in turn alter the solubility of the polymer to developer.

**[0038]** While the technology herein has been described in connection with exemplary illustrative non-limiting embodiments, the invention is not to be limited by the disclosure. The invention is intended to be defined by

the claims and to cover all corresponding and equivalent arrangements whether or not specifically disclosed herein.

## CLAIMS

1. A method of improving the resolution of photolithography comprising incorporating semiconductor nano-sized particles to form highly refractive medium.
2. A method of claim 1 wherein the highly refractive medium is inserted between the photomask and the immediate next lens.
3. A method of claim 1 wherein the highly refractive medium is inserted between the exit lens and the wafer coated with photoresist.
4. A method of claim 1 wherein the inserting is achieved by immersing in the nano-sized particle containing liquid, polymer or gel.
5. A method of claim 4 wherein the liquid contains water.
6. A method of claim 1 wherein the inserting is achieved by continuously flowing the nano-sized particle containing liquid or gel through the space between the last lens and the photoresist coated wafer.
7. A method of claim 6 wherein the liquid contains water.
8. The method of claim 1 wherein the said semiconductor nano-sized particles are selected from the group consisting of C, Si, Ge, CuCl, CuBr, CuI, AgCl, AgBr, AgI, Ag<sub>2</sub>S, CaO, MgO, ZnO, Mg<sub>x</sub>Zn<sub>1-x</sub>O, ZnS, HgS, ZnSe, CdS, CdSe, CdTe, HgTe, PbS, BN, AlN, GaN, Al<sub>x</sub>Ga<sub>1-x</sub>N, GaP, GaAs, GaSb, InP, InAs, In<sub>x</sub>Ga<sub>1-x</sub>As, SiC, Si<sub>1-x</sub>Ge<sub>x</sub>, Si<sub>3</sub>N<sub>4</sub>, ZrN, CaF<sub>2</sub>, YF<sub>3</sub>, Al<sub>2</sub>O<sub>3</sub>, SiO<sub>2</sub>, TiO<sub>2</sub>, Cu<sub>2</sub>O, Zr<sub>2</sub>O<sub>3</sub>, ZrO<sub>2</sub>, SnO<sub>2</sub>, YSi<sub>2</sub>, GaInP<sub>2</sub>, Cd<sub>3</sub>P<sub>2</sub>, Fe<sub>2</sub>S, Cu<sub>2</sub>S, CuIn<sub>2</sub>S<sub>2</sub>, MoS<sub>2</sub>, In<sub>2</sub>S<sub>3</sub>, Bi<sub>2</sub>S<sub>3</sub>, CuIn<sub>2</sub>Se<sub>2</sub>, In<sub>2</sub>Se<sub>3</sub>, HgI<sub>2</sub>, PbI<sub>2</sub>, Landthoids oxides, etc, and their varies alloys.

9. A method of creating an anti-reflection coating on optics a thin layer containing semiconductor nano-sized particle.

10. A method of claim 9 wherein the said semiconductor nano-sized particles are selected from the group consisting of C, Si, Ge, CuCl, CuBr, CuI, AgCl, AgBr, AgI, Ag<sub>2</sub>S, CaO, MgO, ZnO, Mg<sub>x</sub>Zn<sub>1-x</sub>O, ZnS, HgS, ZnSe, CdS, CdSe, CdTe, HgTe, PbS, BN, AlN, GaN, Al<sub>x</sub>Ga<sub>1-x</sub>N, GaP, GaAs, GaSb, InP, InAs, In<sub>x</sub>Ga<sub>1-x</sub>As, SiC, Si<sub>1-x</sub>Ge<sub>x</sub>, Si<sub>3</sub>N<sub>4</sub>, ZnN, CaF<sub>2</sub>, YF<sub>3</sub>, Al<sub>2</sub>O<sub>3</sub>, SiO<sub>2</sub>, TiO<sub>2</sub>, Cu<sub>2</sub>O, Zr<sub>2</sub>O<sub>3</sub>, ZrO<sub>2</sub>, SnO<sub>2</sub>, YSi<sub>2</sub>, GaInP<sub>2</sub>, Cd<sub>3</sub>P<sub>2</sub>, Fe<sub>2</sub>S, Cu<sub>2</sub>S, CuIn<sub>2</sub>S<sub>2</sub>, MoS<sub>2</sub>, In<sub>2</sub>S<sub>3</sub>, Bi<sub>2</sub>S<sub>3</sub>, CuIn<sub>2</sub>Se<sub>2</sub>, In<sub>2</sub>Se<sub>3</sub>, HgI<sub>2</sub>, PbI<sub>2</sub>, Landthoids oxides, etc, and their various alloys.

11. A method of creating pellicle using a thin layer containing semiconductor nano-sized particles.

12. A method of claim 11 wherein the said semiconductor nano-sized particles are selected from the group consisting of C, Si, Ge, CuCl, CuBr, CuI, AgCl, AgBr, AgI, Ag<sub>2</sub>S, CaO, MgO, ZnO, Mg<sub>x</sub>Zn<sub>1-x</sub>O, ZnS, HgS, ZnSe, CdS, CdSe, CdTe, HgTe, PbS, BN, AlN, GaN, Al<sub>x</sub>Ga<sub>1-x</sub>N, GaP, GaAs, GaSb, InP, InAs, In<sub>x</sub>Ga<sub>1-x</sub>As, SiC, Si<sub>1-x</sub>Ge<sub>x</sub>, Si<sub>3</sub>N<sub>4</sub>, ZnN, CaF<sub>2</sub>, YF<sub>3</sub>, Al<sub>2</sub>O<sub>3</sub>, SiO<sub>2</sub>, TiO<sub>2</sub>, Cu<sub>2</sub>O, Zr<sub>2</sub>O<sub>3</sub>, ZrO<sub>2</sub>, SnO<sub>2</sub>, YSi<sub>2</sub>, GaInP<sub>2</sub>, Cd<sub>3</sub>P<sub>2</sub>, Fe<sub>2</sub>S, Cu<sub>2</sub>S, CuIn<sub>2</sub>S<sub>2</sub>, MoS<sub>2</sub>, In<sub>2</sub>S<sub>3</sub>, Bi<sub>2</sub>S<sub>3</sub>, CuIn<sub>2</sub>Se<sub>2</sub>, In<sub>2</sub>Se<sub>3</sub>, HgI<sub>2</sub>, PbI<sub>2</sub>, Landthoids oxides, etc, and their various alloys.

13. A method of using semiconductor nano-sized particles as sensitizer in a photoresist.

14. A method of claim 13 wherein the said semiconductor nano-sized particles are selected from the group consisting of C, Si, Ge, CuCl, CuBr, CuI, AgCl, AgBr, AgI, Ag<sub>2</sub>S, CaO, MgO, ZnO, Mg<sub>x</sub>Zn<sub>1-x</sub>O, ZnS, HgS, ZnSe, CdS, CdSe, CdTe, HgTe, PbS, BN, AlN, GaN, Al<sub>x</sub>Ga<sub>1-x</sub>N, GaP

GaAs, GaSb, InP, InAs,  $\text{In}_x\text{Ga}_{1-x}\text{As}$ , SiC,  $\text{Si}_{1-x}\text{Ge}_x$ ,  $\text{Si}_3\text{N}_4$ , ZrN,  $\text{CaF}_2$ ,  $\text{YF}_3$ ,  $\text{Al}_2\text{O}_3$ ,  $\text{SiO}_2$ ,  $\text{TiO}_2$ ,  $\text{Cu}_2\text{O}$ ,  $\text{Zr}_2\text{O}_3$ ,  $\text{ZrO}_2$ ,  $\text{SnO}_2$ ,  $\text{YSi}_2$ ,  $\text{GaInP}_2$ ,  $\text{Cd}_3\text{P}_2$ ,  $\text{Fe}_2\text{S}$ ,  $\text{Cu}_2\text{S}$ ,  $\text{CuIn}_2\text{S}_2$ ,  $\text{MoS}_2$ ,  $\text{In}_2\text{S}_3$ ,  $\text{Bi}_2\text{S}_3$ ,  $\text{CuIn}_2\text{Se}_2$ ,  $\text{In}_2\text{Se}_3$ ,  $\text{HgI}_2$ ,  $\text{PbI}_2$ , Landthoids oxides, etc, and their various alloys.



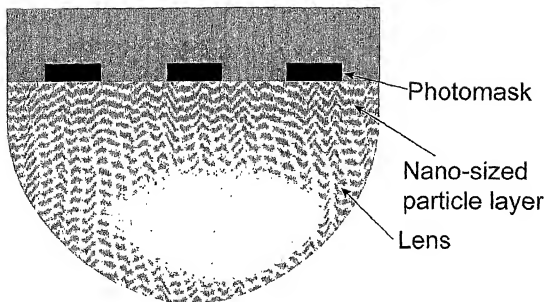


Fig.1

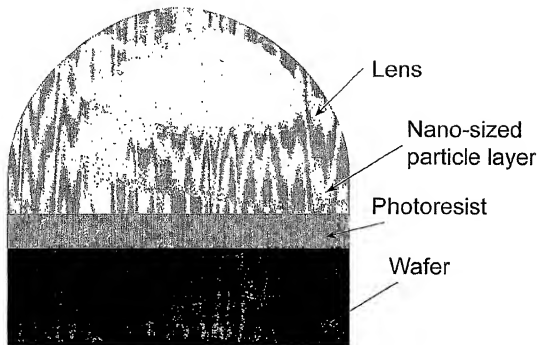


Fig. 2

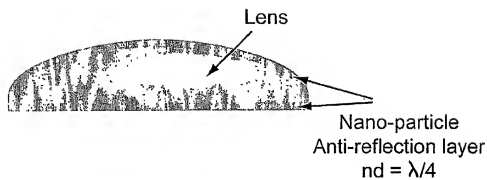
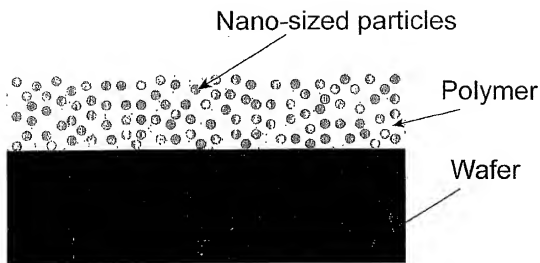
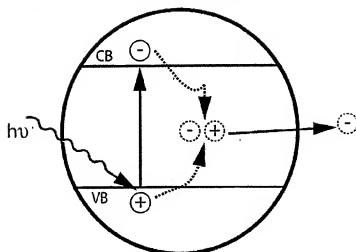


Fig. 3



a)



b)

Fig. 4